SPECIFICATION AMENDMENTS

Page 8, lines 10-12, please amend as follows:

Figs. 3A-3H are illustrations showing an exemplary embodiment
of a writing method according to the invention by application
of a temporally controlled external magnetic field; ~~and~~

Page 8, lines 14-18, please amend as follows:

Fig. 4 is a graph showing the conversion of the method
graphically illustrated in Figs. 3A-3H into a pulse timing
diagram which illustrates the mutually temporally offset
current pulses through the word line and the bit line in each
case when writing a logic "1" and a logic "0"[[.]]; and

Page 8, between lines 18-20, please insert:

--Figs. 5A-5H are illustrations showing an exemplary
embodiment of a writing method for writing a logic "0"
according to the invention by application of a temporally
controlled external magnetic field.--.

Page 13, between lines 23-25, please insert:

--In the graphical representations of Fig. 5A to Fig. 5H, which illustrate the temporal sequence of the rotation of the magnetization when writing a logic "0", for simplification the asteroid is omitted and only the easy axis is indicated by a dashed straight line. As in Figs. 3A-3H, the magnetization of the memory cell MTJ is represented by a bold black arrow and the magnetic field which is composed of the magnetic field components H_y and H_x and is induced by the word line current I_{WL} and the bit line current I_{BL} is represented by a doubly dashed arrow. Fig. 5A illustrates the initial situation. In Figs. 5B and 5C, a magnetic field H_y is first present only in the y-direction, in a manner induced by the currents I_{WL} and I_{BL}, which magnetic field first rotates the magnetization of the MRAM memory cell MTJ through an angle of between 180° and 90° (Fig. 5C). Then, if the two currents I_{WL} and I_{BL} flow, the magnetic field is generated with components H_x and H_y of approximately the same magnitude in the x-direction and y-direction, as a result of which the magnetization direction (bold arrow) rotates further and assumes an angle in the range between 90° and 0° (Fig. 5E). Finally, through a magnetic field which has a component H_x pointing only in the x-direction, the magnetization direction is rotated further in

accordance with Figs. 5F and 5G until it is finally rotated in the x-direction (0°). Fig. 5H shows the de-energized end state, which specifies the information content in accordance with a logic "0" of the MRAM memory cell MTJ.--.